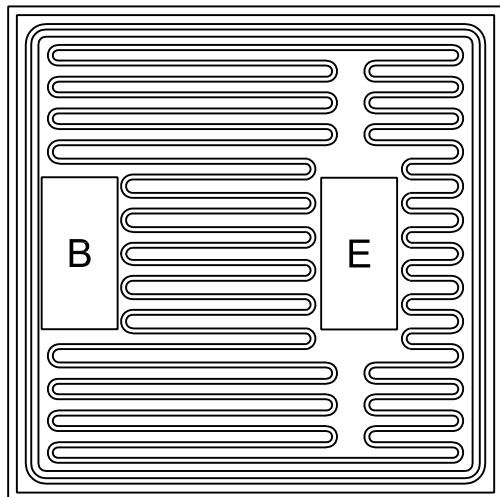


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	51 x 51 MILS
Die Thickness	9.1 MILS
Base Bonding Pad Area	7.9 x 15.7 MILS
Emitter Bonding Pad Area	7.9 x 15.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Ni/Ag - 2000Å/3000Å/20000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

6,480

PRINCIPAL DEVICE TYPES

BUY49S

BSW68

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R0 (12 - June 2006)